



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



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## Product Summary

$BV_{DSS}$	$R_{DS(ON) MAX}$	$I_{D MAX}$ $T_C = +25^{\circ}C$
60V	14m $\Omega$ @ $V_{GS} = 10V$	50.5A
	21m $\Omega$ @ $V_{GS} = 4.5V$	41.2A

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Low  $R_{DS(ON)}$  – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection

## Description and Applications

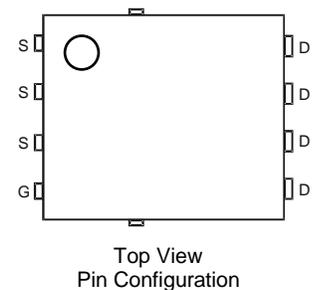
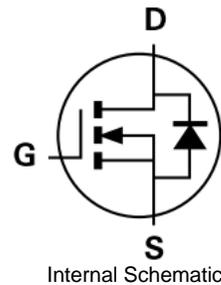
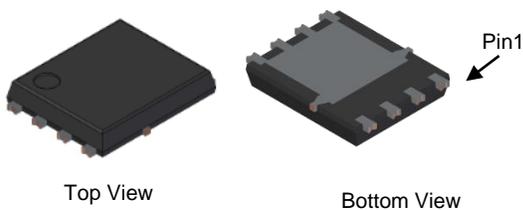
This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Engine management systems
- Body control electronics
- DC-DC converters

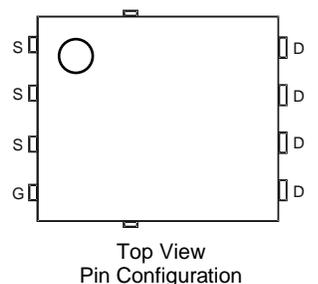
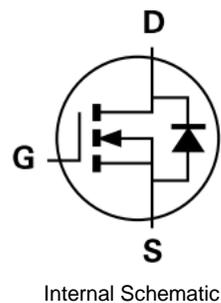
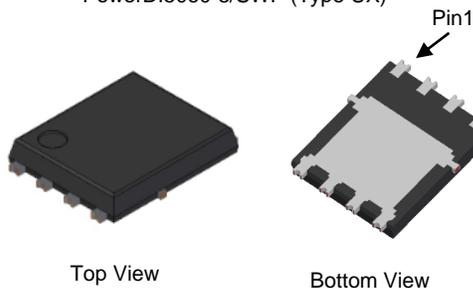
## Mechanical Data

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208  $\text{Ⓢ3}$
- Weight: 0.097 grams (Approximate)

PowerDI5060-8 (SWP) (Type Q)



PowerDI5060-8/SWP (Type UX)



**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)	$I_D$	$T_A = +25^\circ\text{C}$	11.5
		$T_A = +100^\circ\text{C}$	8.1
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	$I_D$	$T_C = +25^\circ\text{C}$	50.5
		$T_C = +100^\circ\text{C}$	35.7
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{DM}$	200	A
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	50	A
Pulsed Body Diode Forward Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{SM}$	200	A
Avalanche Current, $L = 0.1\text{mH}$	$I_{AS}$	12.6	A
Avalanche Energy, $L = 0.1\text{mH}$	$E_{AS}$	7.9	mJ

Notes: 5. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.  
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$ $P_D$	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	54	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	$T_C = +25^\circ\text{C}$ $P_D$	53.6	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	2.8	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$

## Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	2.3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	10.6	14	m $\Omega$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	14.8	21		$V_{GS} = 4.5\text{V}, I_D = 10\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	785	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	281	—		
Reverse Transfer Capacitance	$C_{rss}$	—	27	—		
Gate Resistance	$R_g$	—	1.5	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	—	7.3	—	nC	$V_{DS} = 30\text{V}, I_D = 10\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_g$	—	13.6	—		
Gate-Source Charge	$Q_{gs}$	—	2.2	—		
Gate-Drain Charge	$Q_{gd}$	—	3.4	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.2	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, I_D = 10\text{A}, R_g = 6\Omega$
Turn-On Rise Time	$t_R$	—	4.4	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	14.7	—		
Turn-Off Fall Time	$t_F$	—	8.5	—		
Body Diode Reverse Recovery Time	$t_{RR}$	—	23.0	—	ns	$I_F = 10\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	$Q_{RR}$	—	14.1	—	nC	

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

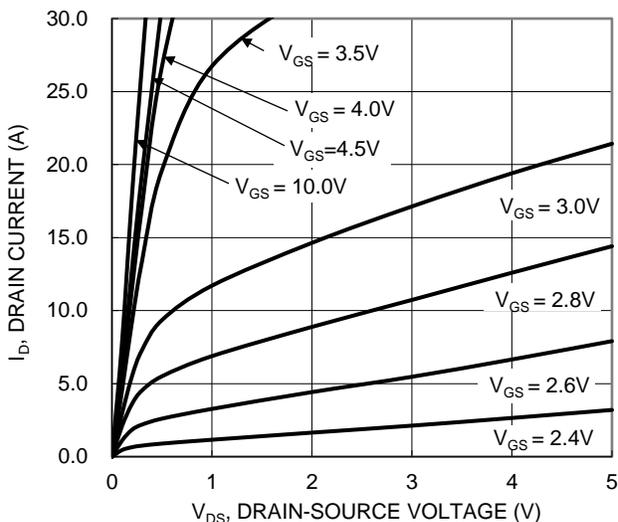


Figure 1. Typical Output Characteristic

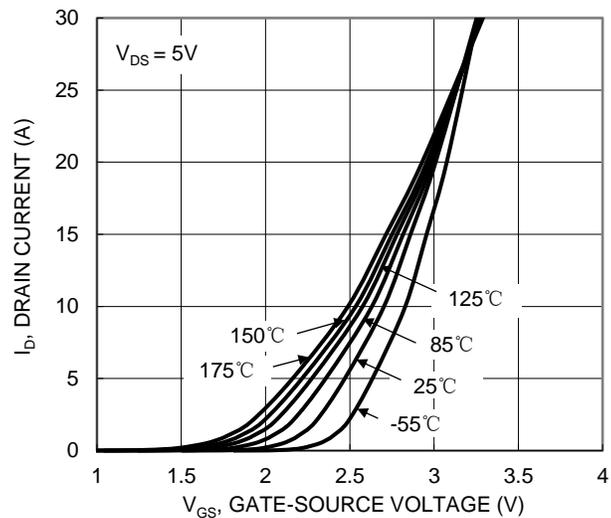


Figure 2. Typical Transfer Characteristic

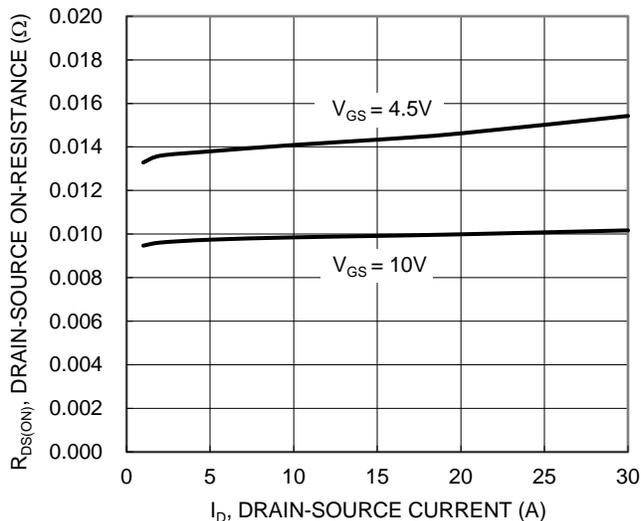


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

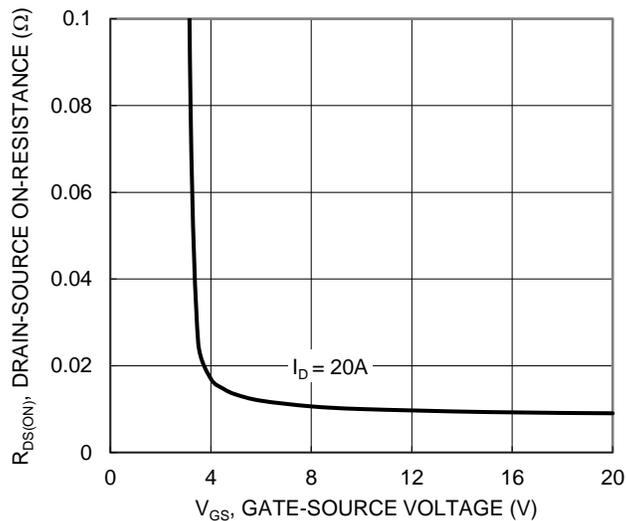


Figure 4. Typical Transfer Characteristic

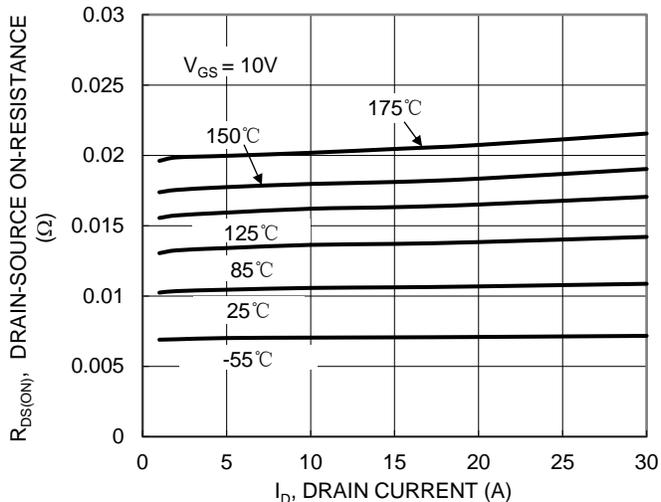


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

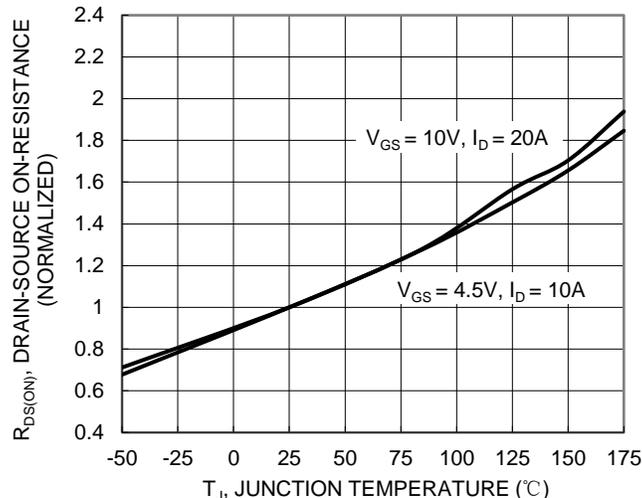


Figure 6. On-Resistance Variation with Temperature

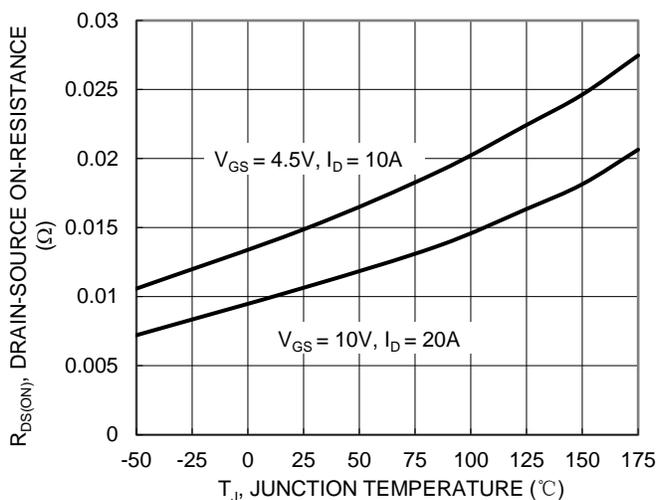


Figure 7. On-Resistance Variation with Temperature

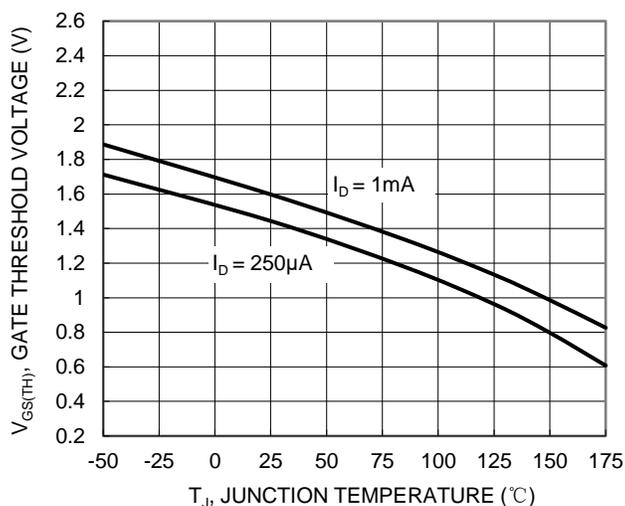


Figure 8. Gate Threshold Variation vs. Junction Temperature

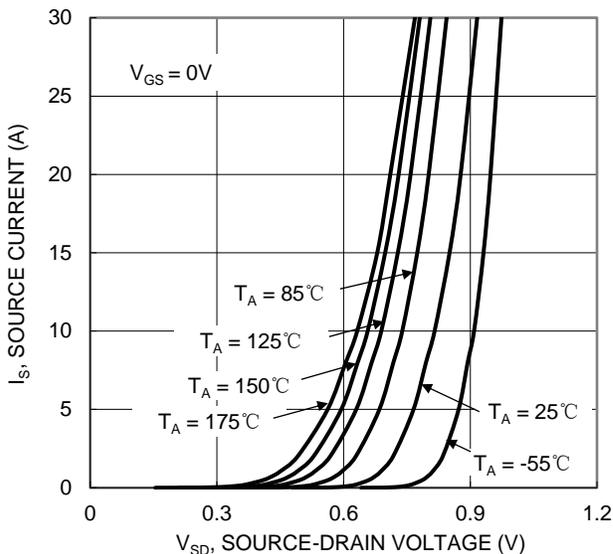


Figure 9. Diode Forward Voltage vs. Current

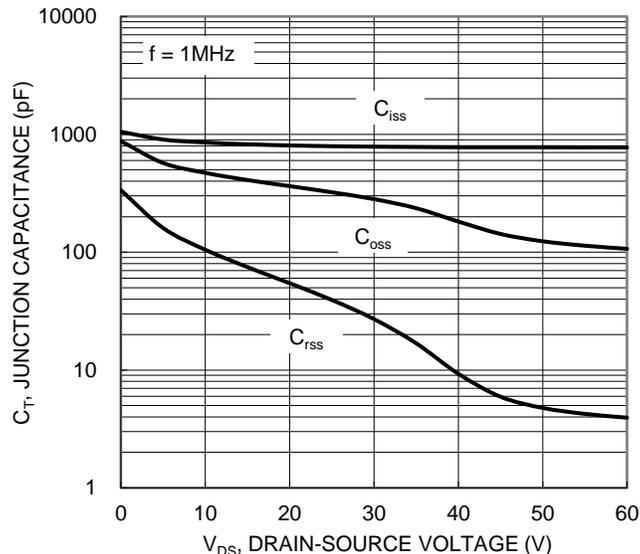


Figure 10. Typical Junction Capacitance

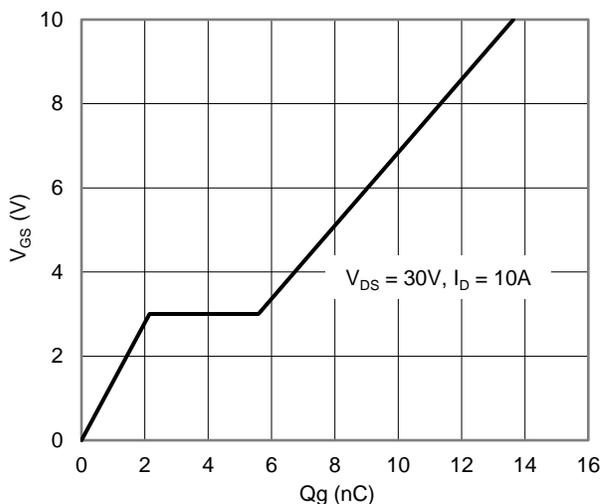


Figure 11. Gate Charge

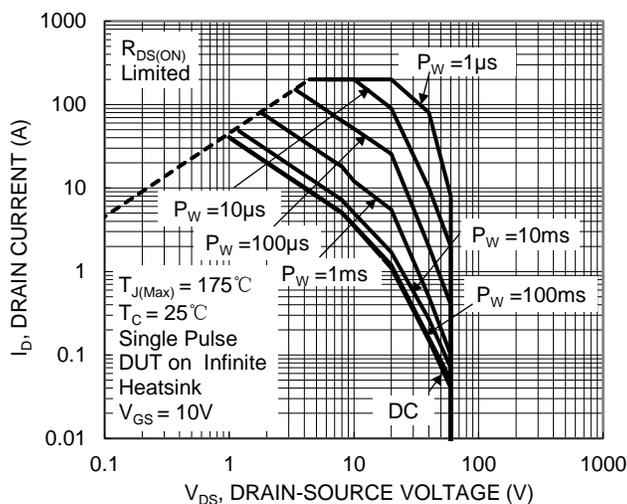
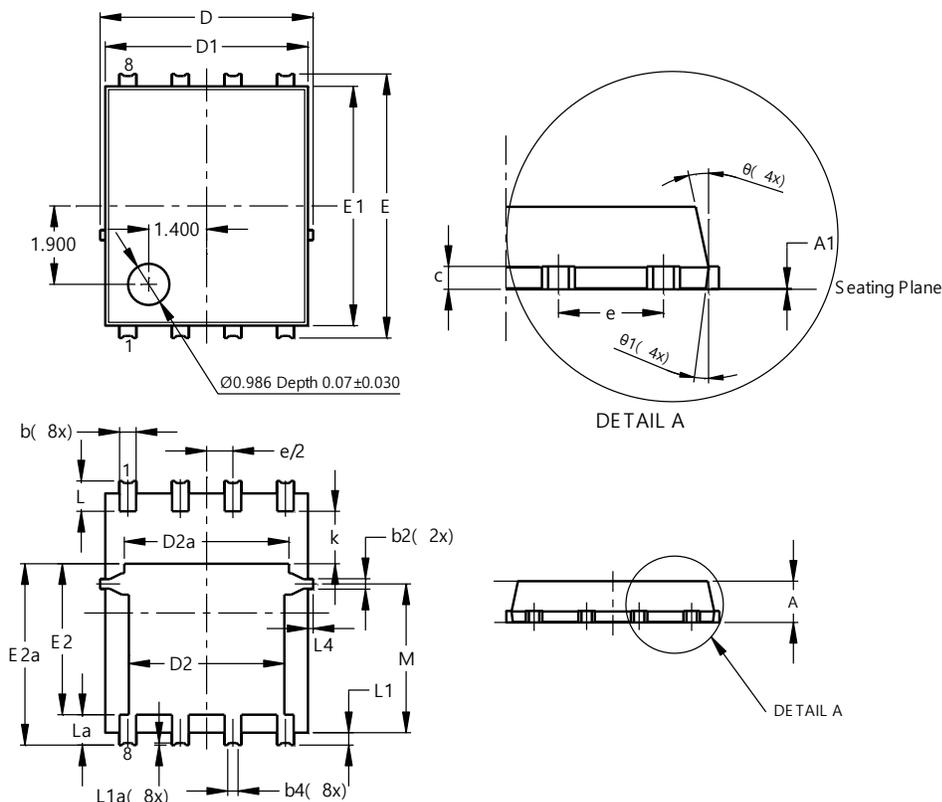


Figure 12. SOA, Safe Operation Area



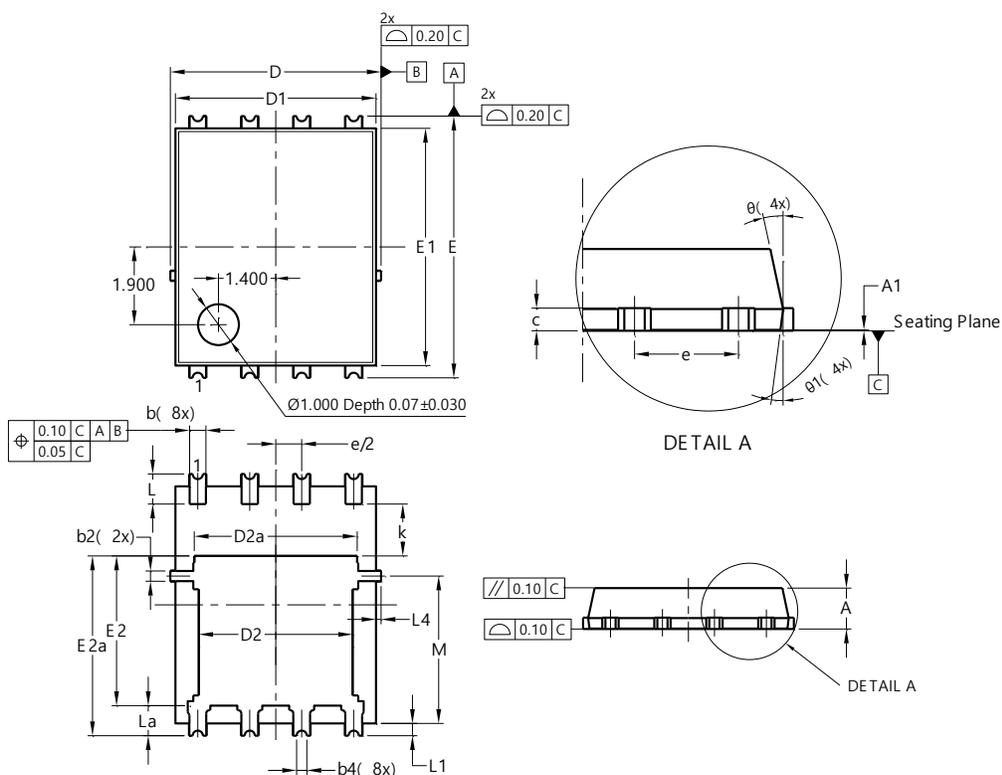
Package Outline Dimensions

PowerDI5060-8 (SWP) (Type Q)



PowerDI5060-8 (SWP) (Type Q)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

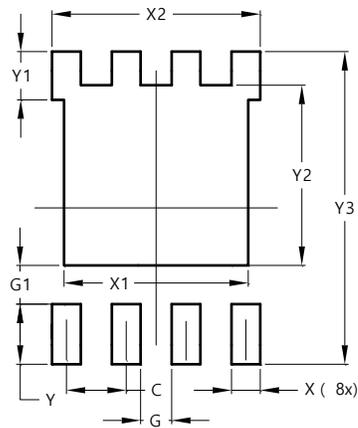
PowerDI5060-8/SWP (Type UX)



PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

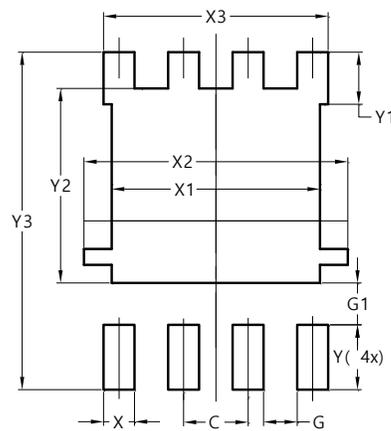
## Suggested Pad Layout

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610